UP04211G

Silicon NPN epitaxial planar type

For switching/digital circuits

Features

- Two elements incorporated into one package (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

Basic Part Number

• UNR2210 \times 2

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	V _{CBO} 50		
Collector-emitter voltage (Base open)	V _{CEO}	50	V	
Collector current	I _C	100	mA	
Total power dissipation	P _T	125	mW	
Junction temperature	Tj	125	°C	
Storage temperature	T _{stg}	-55 to +125	°C	

Package

Code

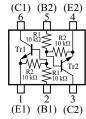
SSMini6-F2

• Pin Name

1: Emitter (Tr1)	4: Emitter (Tr2)
2: Base (Tr1)	5: Base (Tr2)
3: Collector (Tr2)	6: Collector (Tr1)

■ Marking Symbol: 9V

Internal Connection



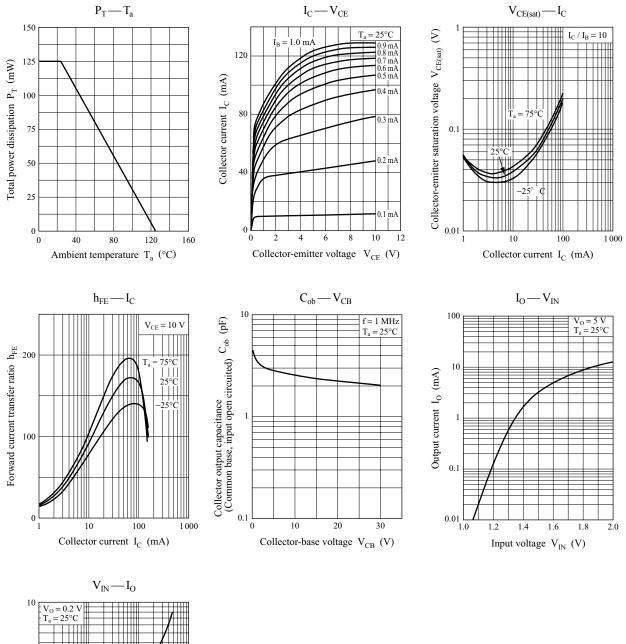
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

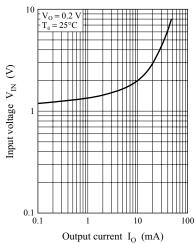
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 {\rm mA}, I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 50 \text{ V}, I_{B} = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{\rm EB} = 6 \rm V, I_{\rm C} = 0$			0.5	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	35			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.3 \text{ mA}$			0.25	V
Output voltage high-level	V _{OH}	$V_{\rm CC} = 5 \text{ V}, V_{\rm B} = 0.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$	4.9			V
Output voltage low-level	V _{OL}	$V_{\rm CC} = 5 \text{ V}, V_{\rm B} = 2.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$			0.2	V
Input resistance	R ₁		-30%	10	+30%	kΩ
Resistance ratio	R_1/R_2		0.8	1.0	1.2	
Transition frequency	\mathbf{f}_{T}	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

UP04211G

Panasonic



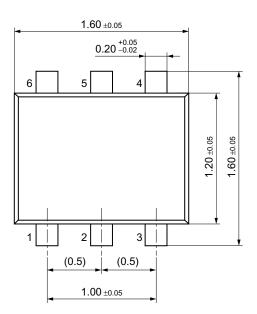


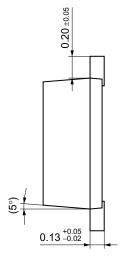
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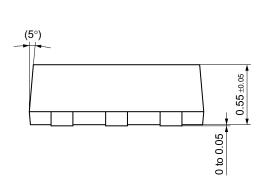
Panasonic

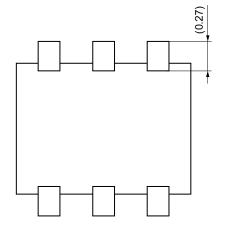
SSMini6-F2

Unit: mm









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